

November 2013

## FDPF4N60NZ

# N-Channel UniFET<sup>TM</sup> II MOSFET 600 V, 3.8 A, 2.5 $\Omega$

## **Features**

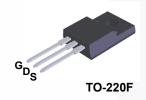
- $R_{DS(on)}$  = 1.9  $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.9 A
- Low Gate Charge (Typ. 8.3 nC)
- Low C<sub>rss</sub> (Typ. 3.7 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · ESD Improved Capability
- · RoHS Compliant

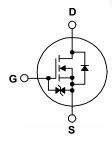
## **Applications**

- · Consumer Appliances
- Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

## Description

UniFET<sup>TM</sup> II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts





## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FDPF4N60NZ	Unit
V <sub>DSS</sub>	Drain to Source Voltage		600	V	
V <sub>GSS</sub>	Gate to Source Voltage			±25	V
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		3.8*	^
ID	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		2.3*	Α
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	15*	Α
E <sub>AS</sub>	Single Pulsed Avalanche Ene	ergy	(Note 2)	223.8	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	3.8	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1		(Note 1)	8.9	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	10	V/ns
D	Dower Dissination	(T <sub>C</sub> = 25°C)		28	W
$P_{D}$	Power Dissipation	- Derate Above 25°C		0.22	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5	Seconds	300	°C

<sup>\*</sup>Drain current limited by maximum junction temperature.

## **Thermal Characteristics**

Symbol	Parameter FDPF4N60NZ		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	- 0/00

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF4N60NZ	FDPF4N60NZ	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	600	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	-	-	1	
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	-	-	±10	μΑ

## **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.9 A	-	1.9	2.5	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 1.9 A	-	3.3	-	S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V = 25 V V = 0 V	-	385	510	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1  MHz		40	60	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-\	3.7	5	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 480 V I <sub>D</sub> = 3.8 A,	-	8.3	10.8	nC
Q <sub>gs</sub>		V <sub>GS</sub> = 10 V	-	2.1	-	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	(Note 4)	-	3.3	-	nC

## **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time			-	12.7	35.4	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_{D} = 3.8 \text{ A},$		-	15.1	40.2	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$		- /	30.2	70.4	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4)	-	12.8	35.6	ns

## **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode	Maximum Continuous Drain to Source Diode Forward Current		-	3.8*	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	15	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3.8 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3.8 A,	-	168	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	0.7	/ -	μС

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 31 mH, I<sub>AS</sub> = 3.8 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3.  $I_{SD} \le 3.8$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

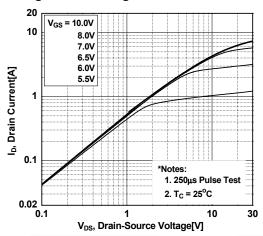


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

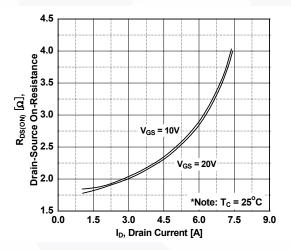


Figure 5. Capacitance Characteristics

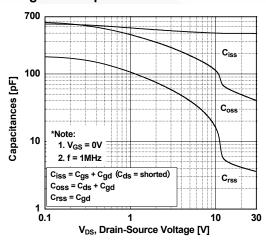


Figure 2. Transfer Characteristics

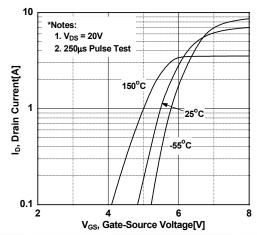


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

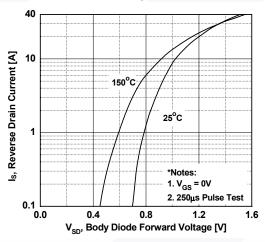
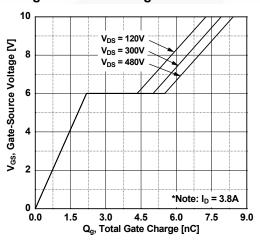


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

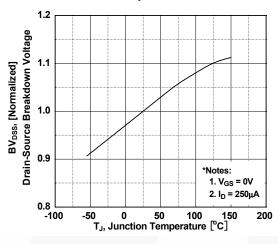


Figure 9. Maximum Safe Operating Area

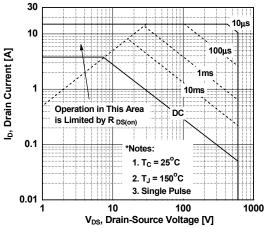


Figure 11. Unclamped Inductive Switching Capability

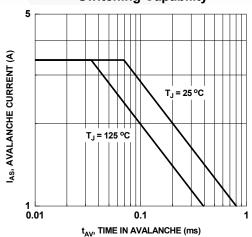


Figure 8. On-Resistance Variation vs. Temperature

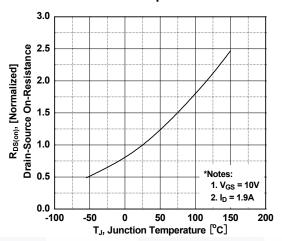
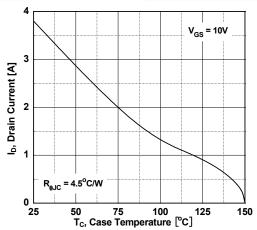
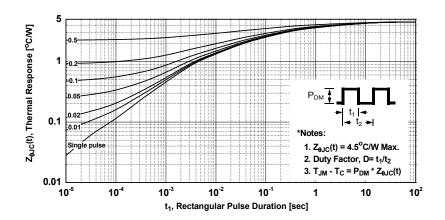


Figure 10. Maximum Drain Current vs. Case Temperature



## **Typical Performance Characteristics** (Continued)

Figure 12. Transient Thermal Response Curve



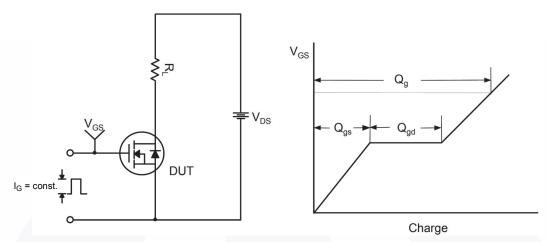


Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

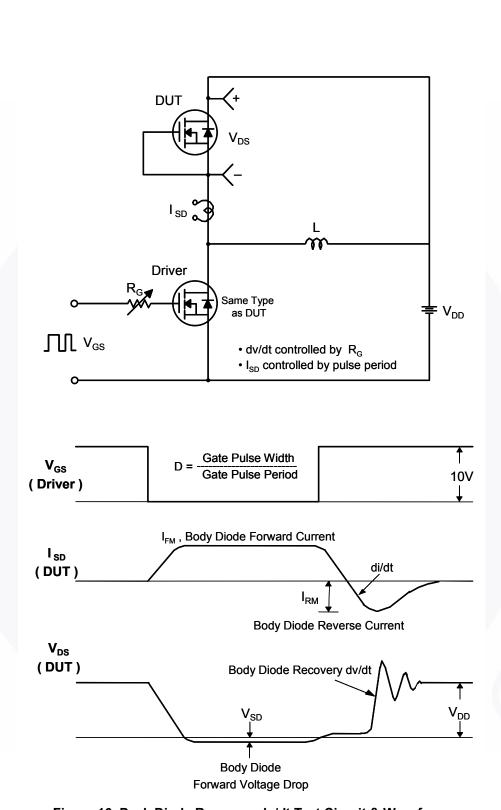


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

## **Mechanical Dimensions**

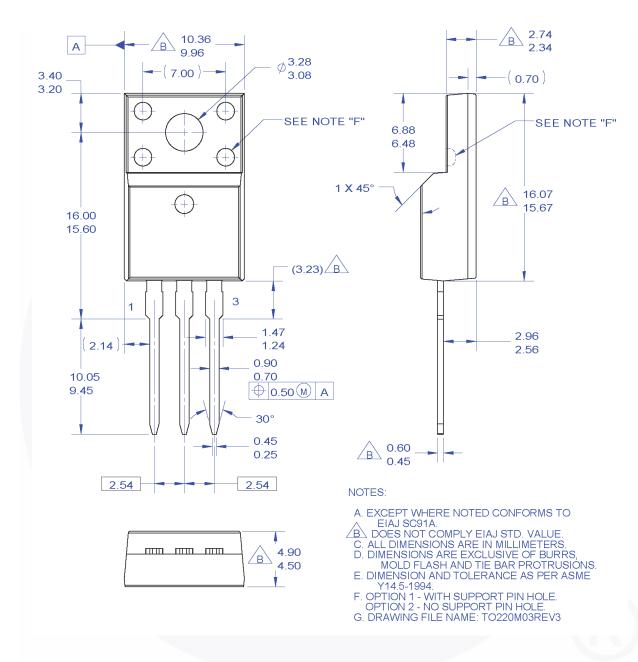


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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